ADE-208-321(Z)

HVU132
Silicon Epitaxial Planar Pin Diode for Antenna Switching

HITACHI

Rev. 0
Feb. 1995

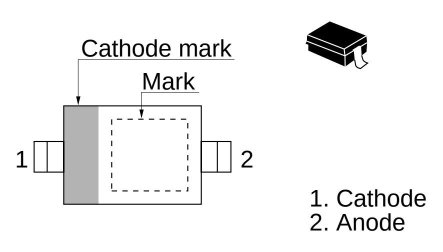
Features

- Low capacitance.(C=0.5pF max)
- Low forward resistance. (r_f=2.0Ω max)
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVU132	P2	URP

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F	100	mA
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	I_F = 10 mA
Reverse current	I_R	—	—	0.1	µA	V_R = 60 V
Capacitance	C	—	—	0.5	pF	V_R = 1 V, f = 1 MHz
Forward resistance	r_f	—	—	2.0	Ω	I_F = 10 mA, f = 100 MHz

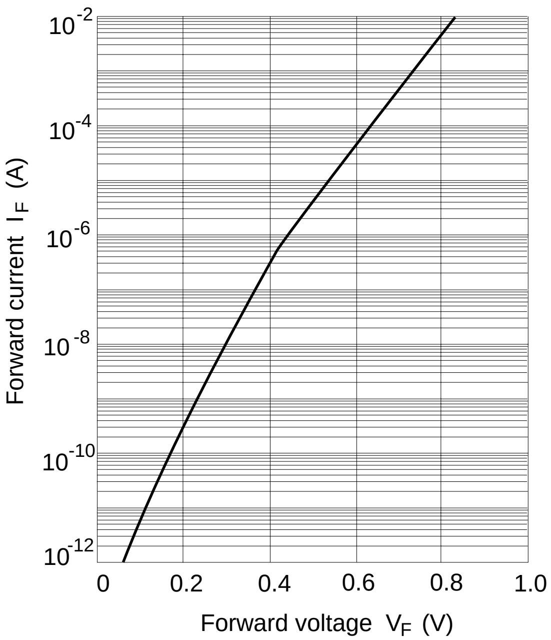


Fig.1 Forward current Vs. Forward voltage

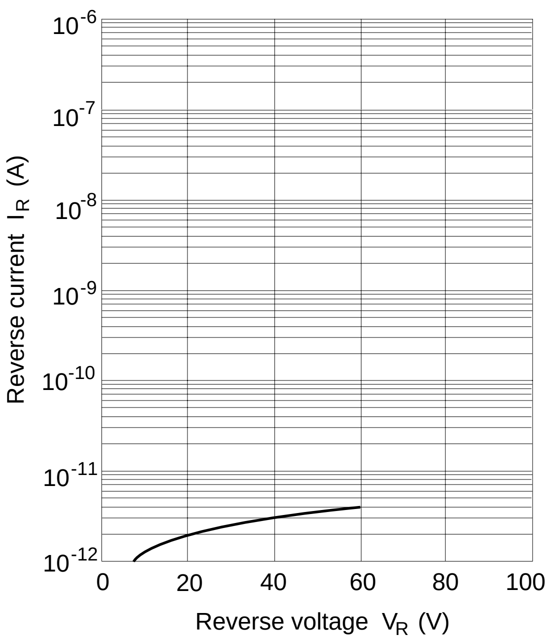


Fig.2 Reverse current Vs. Reverse voltage

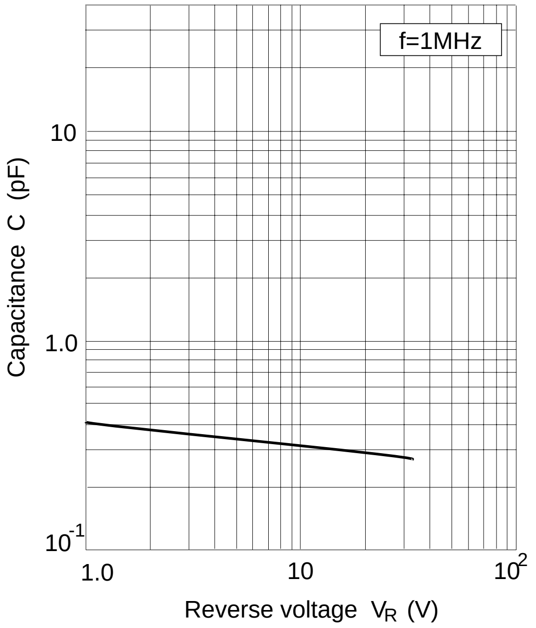


Fig.3 Capacitance Vs. Reverse voltage

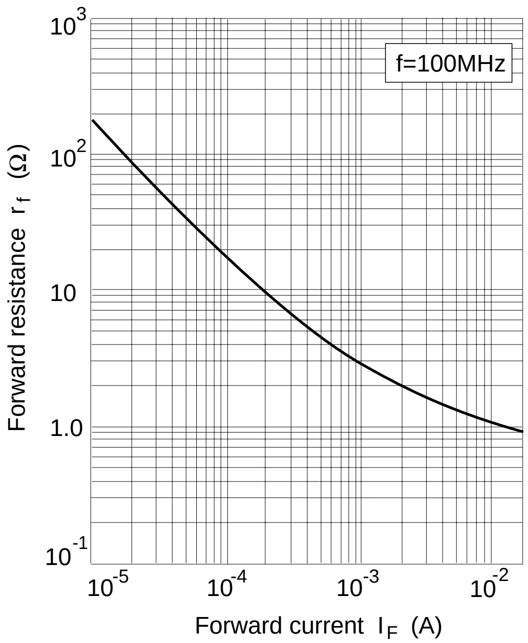
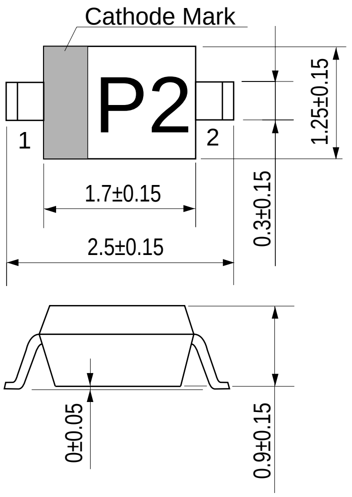


Fig.4 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm



1 Cathode
2 Anode

HITACHI Code	URP
JEDEC Code	—
EIAJ Code	—
Weight (g)	0.004